

Quantum interference in nanometric devices: ballistic transport across arrays of T-shaped quantum wires

Guido G. Goldoni, Fausto Rossi, Elisa Molinari

Istituto Nazionale per la Fisica della Materia (INFM), and

Dipartimento di Fisica, Università di Modena, Via Campi 213/A, I-41100 Modena, Italy
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We propose that the recently realized T-shaped semiconductor quantum wires (T-wires) could be exploited as three-terminal quantum interference devices. T-wires are formed by intersecting two quantum wells (QWs). By use of a scattering matrix approach and the Landauer-Buttiker theory, we calculate the conductance for ballistic transport in the parent QWs and across the wire region as a function of the injection energy. We show that different conductance profiles can be selected by tailoring the widths of the QWs and/or combining more wires on the scale of the Fermi wavelength. Finally, we discuss the possibility of obtaining spin-dependent conductance of ballistic holes in the same structures.

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T-shaped quantum wires (T-wires) are semiconductor structures where quasi-one-dimensional (q1D) confinement is achieved at the intersection between two quantum wells (QWs).¹ T-wires are obtained by first growing a GaAs/Al_xGa_{1-x}As superlattice (labelled QW 1) on a (001) substrate; after cleavage, a GaAs QW (labelled QW 2) is grown over the exposed (110) surface, resulting in an array of T-shaped regions where electron and hole wavefunctions can be confined on a scale of few (5-10) nm. Up to now, the intensive investigation of these structures focussed on optical properties, and demonstrated strong one-dimensional quantum confinement of the lowest excitonic transitions² as well as evidence of laser emission.³ Transport experiments along the wires were first obtained very recently.⁴

At difference with wires obtained by other techniques, such as V-shaped or deep-etched wires,⁵ the section of a T-wire has an open geometry. Therefore, in addition to transport along the quantum wire in the q1D bound states, parallel transport in the constituent QWs and across the wire region becomes possible if the two-dimensional (2D) continuum is contacted (for example through the overgrown layer). In addition to q1D bound states, falling below the 2D continuum edge of the parent QWs, q1D resonant states exist within the 2D continuum.⁶ The injected carriers that travel ballistically over the wire region (nm scale) will show a strongly energy dependent transmission, as a consequence of quantum interference effects induced either by resonant q1D states or by the interplay between the propagating modes of the parent QWs.

In semiconductors, quantum interference effects are normally achieved in channels defined by gating an underlying 2D high mobility electron gas with electrostatic potentials. Structures of this type with T-shaped geometries have been proposed to achieve device functions;⁷ in this case, the conductance along a channel can be controlled by modulating the length of a lateral, closed arm (stub).^{8;9} In the present T-wires, instead, the lateral

arm (QW 1) is open, and the conductance is controlled by modulating the chemical potential (i.e. the injection energy); as we will show, different shapes of the conductance as a function of energy can be selected by tailoring the widths of the QWs and/or combining more wires. In the proposed experiment with T-wires, the interference patterns should be stable in a much larger temperature range than in previously proposed structures, due to the nm-size confinement and the large inter-subband splittings in the parent QWs (of the order of 0.1 eV); furthermore, the confinement is provided by high-quality interfaces, as demonstrated by the small excitonic linewidths.²

In the following we calculate the ballistic conductance for parallel transport in the QWs through the T-wire intersection. Assuming perfect barrier confinement in the parent QWs, the calculation of the scattering matrix¹⁰ presents no conceptual difficulty. We divide the sample in four regions (see inset of Fig. 1); in each region the wavefunction of energy E is written as a linear combination of the propagating and evanescent modes of the corresponding QW. Indicating with $E_{1,m}$ and $f_{1,m}(x)$ the subband energies and envelope functions of QW 1, and with $E_{2,m}$ and $f_{2,m}(y)$ those of QW 2, we have, for zero in-wire momentum,

$$A = \sum_X f_{2,m}(y) a_n^> e^{i n x} + a_n^< e^{-i n x}; \quad (1a)$$

$$B = \sum_X^n f_{1,m}(x) b_n^< e^{i n y} + b_n^> e^{-i n y}; \quad (1b)$$

$$C = \sum_X^n f_{2,m}(y) c_n^< e^{i n x} + c_n^> e^{-i n x}; \quad (1c)$$

$$D = \sum_X^n f_{2,m}(y) d_n^+ e^{i n x} + d_n^- e^{-i n x} + \sum_n f_{1,m}(x) e_n^- e^{i n y} - e_n^+ e^{-i n y}; \quad (1d)$$

where the wavevectors k_n ; k_{-n} are given by $k_n^2 =$

$n^2 = (L_2)^2$ and $\frac{2}{n} = \frac{2}{L_2} = \frac{2}{L_1} = \frac{2}{L_2}$. Here, $E = E_{2,1}$ is the energy in units of the lowest mode of QW 2, $E_{2,1} = \hbar^2 \frac{2}{2m L_2^2}$, and $L_1 = L_2$. The two equations obtained at each interface by matching both the wave function and its normal derivative are projected over the n th mode (i.e., multiplied by the appropriate sine or cosine function and integrated over the interface) and finally summed and subtracted to obtain two new equations, relating either the incoming or the outgoing wave coefficient through that interface to the coefficients of the inside region D. Including N modes¹¹ in the sums in (1a)–(1d), and defining the vector $a^> = (a_1^>; a_2^>; \dots)$, and analogously for the other coefficients, we obtain a set of linear equations of the form

$$a^< = d^+ + P^- e^-; \quad (2a)$$

$$b^> = V^- d^+ + W^- d^- + e^-; \quad (2b)$$

$$c^< = d^+ + Q^- e^-; \quad (2c)$$

where the eight $N \times N$ matrices P^- , Q^- , V^- , and W^- ensue from the matching conditions and depend on the geometrical parameters and on the energy. By defining the incoming and outgoing states $j_{in} = (a^>; b^>; c^>)$ and $j_{out} = (a^<; b^<; c^<)$, and appropriate $3N \times 3N$ matrices F^- , G^- in terms of the eight matrices above, the Eqs. (2a)–(2c) can be rewritten as

$$j_{out} = F^- e^-; d^+; d^-^T; j_{in} = G^- e^-; d^+; d^-^T; \quad (3)$$

Combining Eqs. (3) we finally get

$$j_{out} = F^- G^{-1} j_{in} = S^- j_{in}; \quad (4)$$

Equation (4) defines the scattering matrix S^- , which gives at the same time the bound state (< 1)¹² satisfying the equation $\det S^- = 0$, and the scattering states (> 1).

Since the scattering matrix is a property of the potential at a given energy, it allows to calculate all transmission coefficients, say from mode n in arm A to mode m in arm C, by the same matrix, choosing the appropriate state j_{in} ; to keep on with the example of A \rightarrow C transmission, the transmission coefficient is $t_{nm}^{A \rightarrow C} = j_n^< = a_m^> j_n = m$. In the following we shall concentrate on straight (i.e., A \rightarrow C) transmission along QW 2. We consider a configuration in which arm B is kept at the same potential of arm C ($V_B = V_C$). Therefore, no carrier is injected into the structure through arm B, and $b^> = 0$.¹³ Using one of the Eqs. (2b), we can eliminate the coefficients e^- from the equations and we can rewrite (2a), (2c) as

$$\begin{pmatrix} c^< \\ a^< \end{pmatrix} = T^- \begin{pmatrix} a^> \\ a^< \end{pmatrix}; \quad (5)$$

where T^- is the $2N \times 2N$ A \rightarrow C transfer matrix. Note that if $V_B > V_C$, a case which we shall not investigate here, a certain amount of charge would be incoherently injected in the system through arm B, and the transfer

matrix would then contain an incoherent part which, in a three-terminal device, has been discussed by Buttiker¹⁴; in Ref. 14 the ratio between the coherent and incoherent parts of a two-terminal conductance is modulated through the tunneling probability into a third, randomizing terminal. The present T-shaped wires with $V_B > V_C$ might in fact be a system to implement such an experiment, with the tunneling probability into arm B being adjusted through the injection energy.

Going back to the $V_B = V_C$ case, the two-terminal Landauer-Buttiker (LB) conductance¹⁵ is

$$g = \frac{2e^2}{h} \sum_{i,j} t_{i,j}^{A \rightarrow C}; \quad (6)$$

In Fig. 1 we show the dimensionless conductance $g = \frac{2e^2}{h}$ as a function of the energy and for selected values of the parameter L_b . We recognize two types of behaviours: for samples in which the width of side arm, QW 1, matches an integer number of semiperiods of the incoming wave ($L_b = 0.5, 1, 1.5$, left panels) there are strong reflection resonances¹⁶ at the energies of resonant q1D states localized at the intersection; when these states appear, their energy is at or slightly below the onset of a new propagating state along QW 2 which, in the present units, is at $n^2 = 1; 4; 9; \dots$. When the matching condition is not fulfilled ($L_b = 0.75, 1.25, 1.75$, right panels), the conductance shows, on top of a regular increase, a square-wave behaviour, with sudden drops and rises when new propagating channels open in QW 1 or QW 2, i.e., the current coming from arm A flows into the side arm B or into the straight arm C, depending on the energy.

If successive wires in an array are at a distance larger than the coherence length, incoherent scattering will redistribute carriers homogeneously among the propagating modes; therefore, the conductance of N incoherently coupled wires is G^N , apart from possible broadening due to fluctuations in the QW widths on the monolayer scale; this would not wash out completely the interference patterns, however, as long as the intersubband splittings are large. Conversely, the LB conductance of a single wire can be changed by coupling more wires on the scale of the Fermi wavelength; this possibility is a distinct advantage of structures grown by epitaxy. As an example, we consider two coupled T-wires with a barrier of width L_d between two QW 1s (see inset in Fig. 2). The transmission coefficient of the whole structure can be easily calculated, as the total T^- matrix is the product of the T^- matrices of the isolated wires. In Fig. 2(a) we compare, for the case $L_b = 0.5$, the conductance of a single wire with the conductance of two coupled wires for $L_b = L_1$ and $L_b = 2L_1$. In the first case, the conductance shows a double resonance, which is a fingerprint of the bonding and antibonding combinations of the resonant q1D state of the isolated wires. In the second case, instead, the resonance is completely suppressed. In Fig. 2(b) we compare, for the case $L_b = 1.2$, the single and coupled wire

conductance with $L_b = L_1=2$ and $L_b = 2L_1=3$. The coupled wire case shows sharper modulations with respect to the isolated wire case.

Finally, we consider the possibility of transmitting holes, instead of conduction electrons, through a T-wire. The valence subbands of a T-wire are strongly spin-split at finite in-wire wavevectors.⁶ This can be understood in the following way: if the parent QWs of a T-wire were isolated, the spin-degenerate valence subbands would be degenerate at some finite in-wire wavevector, because of the different effective masses for (001)- and (110)-grown wells. In each QW valence states can be characterized with the component of the total angular momentum $J = 3/2$, the J quantization axis being along the growth direction.¹⁷ Therefore, a state with a well defined component J_z , say $J_z = 3/2$ in one QW, is a mixture of $J_z = 3/2; 1/2$ states in the other QW; as a consequence, the strong spin-orbit coupling of valence states, by coupling heavy hole (i.e., $J_z = 3/2$) and light hole (i.e., $J_z = 1/2$) states removes the degeneracy and results in a large spin-splitting.⁶ Therefore, if holes cross the wire region having a finite component of the wavevector along the wire axis, the transmitted current at selected energies could be strongly spin-polarized.

In summary, we have proposed a nanostructure interference device based on cleaved-edge-overgrown T-shaped quantum wires, and shown that its conductance profile can be tailored by choosing appropriate widths of the constituent QWs and of the barriers between adjacent structures. Possible applications as spin-selective devices for holes were also proposed, and will require further theoretical and experimental investigations.

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⁵ For a review see e.g. R. Cingolani and R. Rinaldi, Rivista Nuovo Cimento 16, 1 (1993).

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⁹ Note the different dimensionality of the devices obtained by gating a 2D electron gas with respect to the device proposed here: In Refs. 7,8 the lateral arms of the T are q1D channels, therefore termed "wires". In T-wires obtained by cleaved edge overgrowth, the lateral arms of the T are sections of 2D systems, and the term "wire" refers to the q1D nature of the states localized at the intersection of such QWs.

¹⁰ See, for example, E. Merzbacher, Quantum Mechanics (Wiley International Edition, New York, 1970), p. 93.

¹¹ In principle, Eqs. (2a)-(2c) can only be satisfied by an infinite number of modes, which means that we have to check the convergence of our results with respect to N . In practice, since the energy of each mode increases as n^2 in a finite well, very few modes are necessary.

¹² For a wire with $L_1 = L_2$, the bound state is always at $\epsilon = 0.807$; when the parent QWs are different, $0.807 < \epsilon < 1$.

¹³ If arm B were terminated by a perfectly reflecting wall at a distance L , as in Refs. 7,8, we should set $b_n^> = b_n^< \exp(2i n L)$ to account for the phase accumulated going along arm B.

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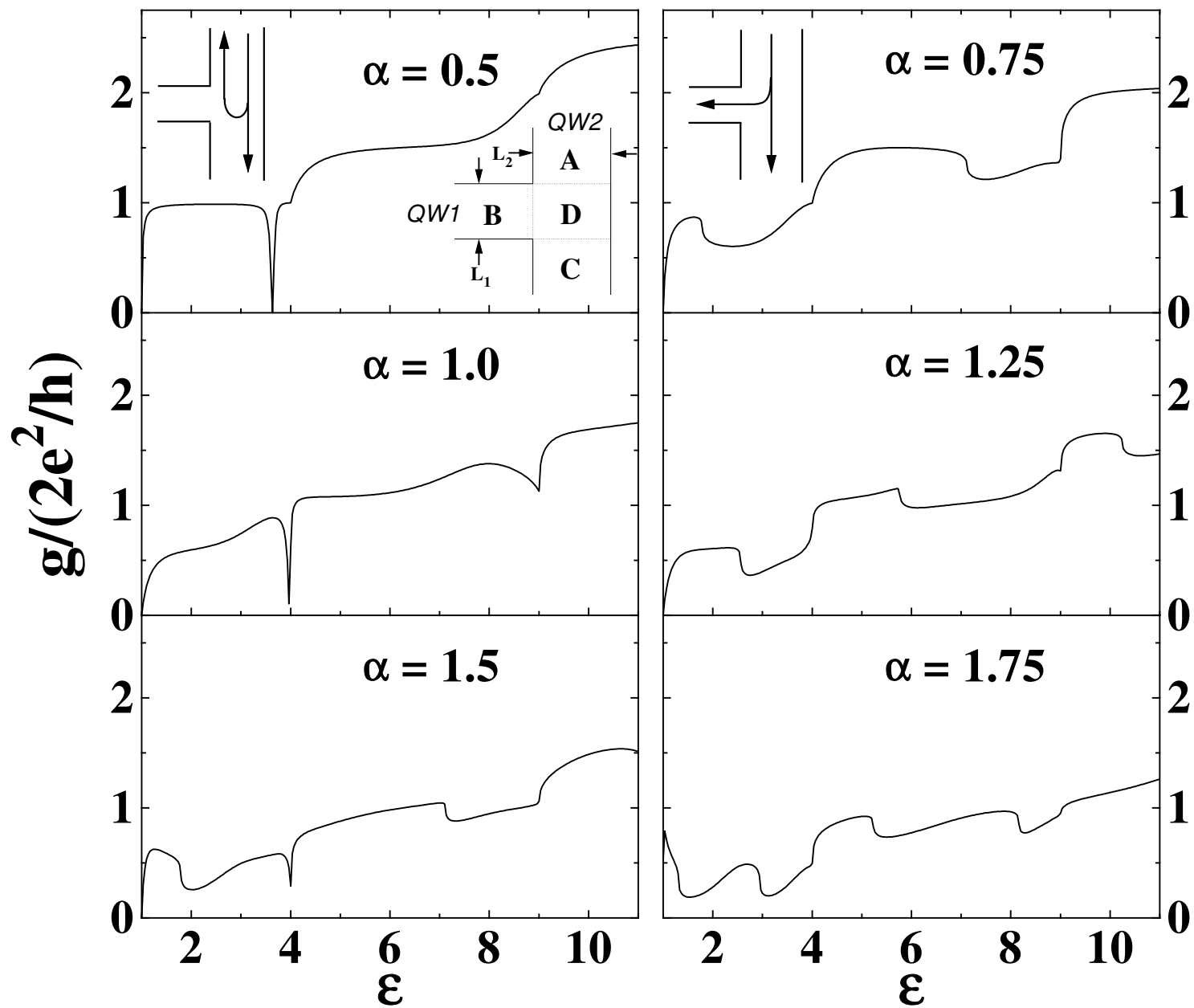
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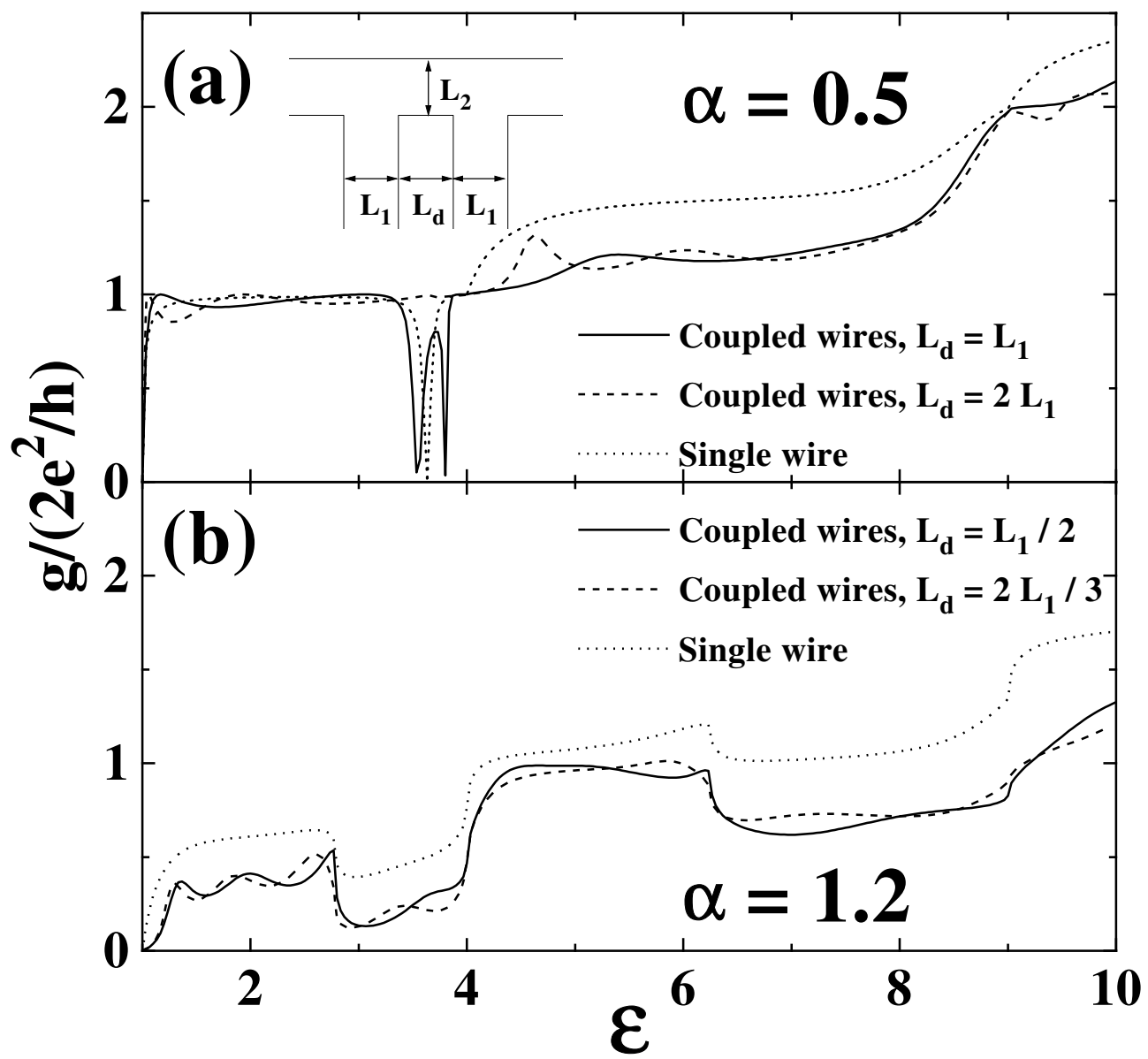
¹⁷ G. Bastard, Wave mechanics applied to semiconductor heterostructures (Les editions des physique, Les Ulis, Paris, France 1988), p. 101.

FIG. 1. Two-terminal conductance vs injection energy for selected values of ϵ , according to the labels. The relevant geometric parameters are defined in the inset.

FIG. 2. Two-terminal conductance vs injection energy for a single wire and for two coupled wires for a) $\epsilon = 0.5$ and b) $\epsilon = 1.2$ and for selected values of L_b . The relevant geometric parameters are defined in the inset.



G. Goldoni et al - Fig. 1



G. Goldoni et al. - Fig. 2

